



**Product data sheet** 

### 1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

### 2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Isolated package
- Less sensitive gate for improved noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

#### 3. Applications

- General purpose motor control
- General purpose switching

#### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	95	A
Tj	junction temperature		-	-	125	°C
$\mathbf{I}_{\mathrm{T(RMS)}}$	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 56 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	-	12	A
Static ch	aracteristics		· · ·			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	8	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	10	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>	-	22	70	mA

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	250	-	V/µs

# 5. Pinning information

Table 2. F	Pinning infor			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		
3	G	gate		T2-T1
mb	n.c.	mounting base; isolated		sym051

# 6. Ordering information

Table 3. Ordering information						
Type number	Package	9				
	Name	Description	Version			
BT138X-800	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BT138X-800	BT138X-800

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 56 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	12	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	95	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	105	A
l <sup>2</sup> t	l <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	45	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA; T2+ G+	-	50	A/µs
		I <sub>G</sub> = 70 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 70 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 140 mA; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

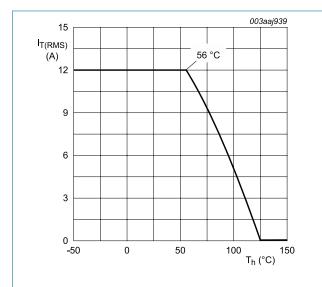
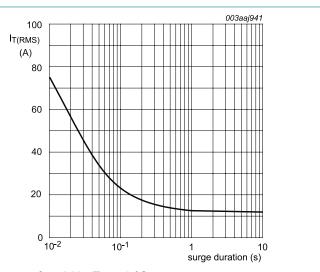
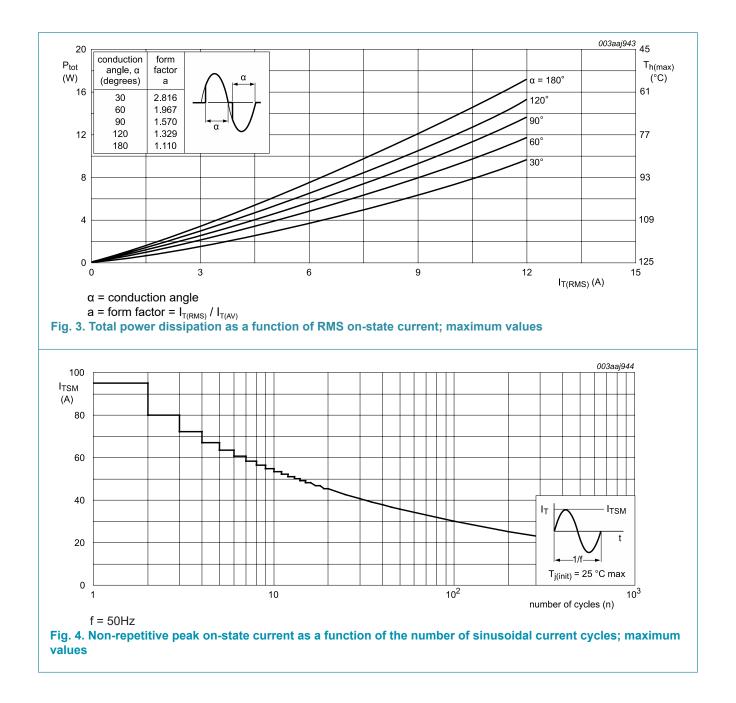


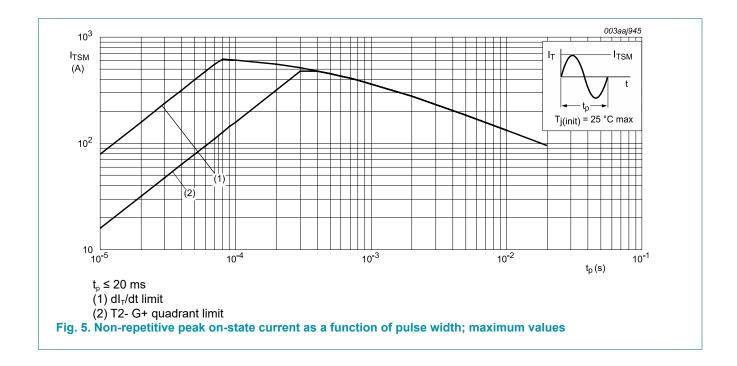
Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values





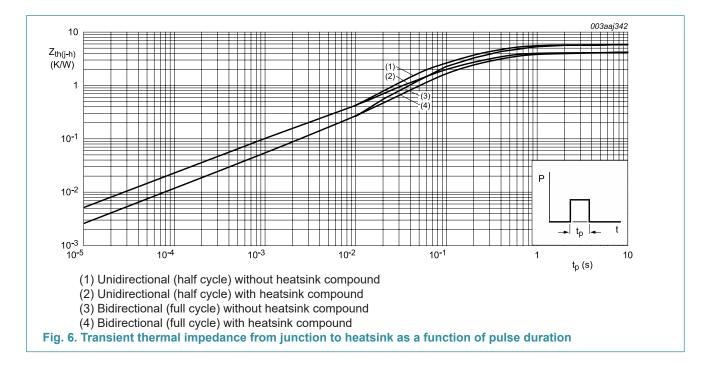
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-h)}}$	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig. 6	-	-	4	K/W
	heatsink	full or half cycle; without heatsink compound; Fig. 6	-	-	5.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



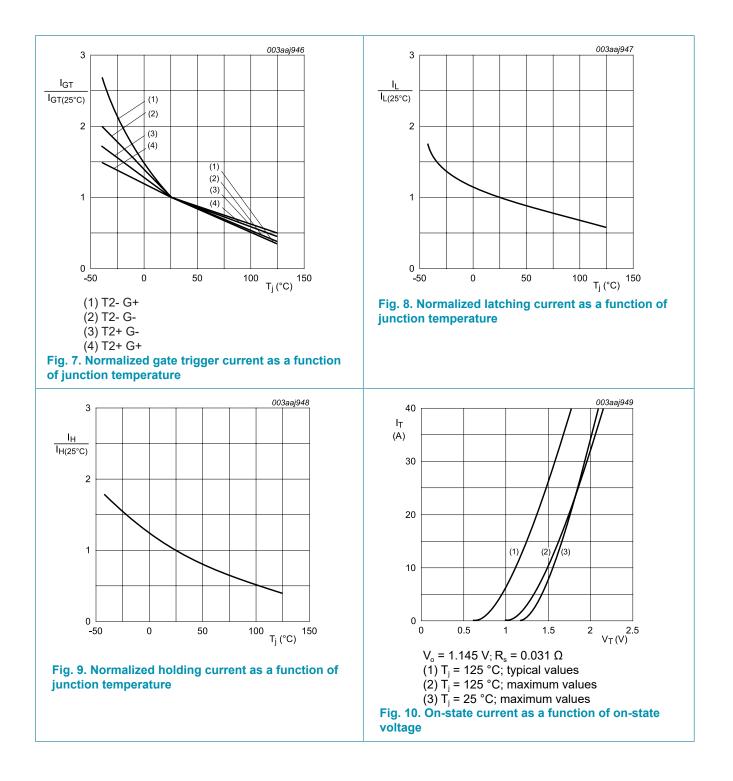


### **10. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

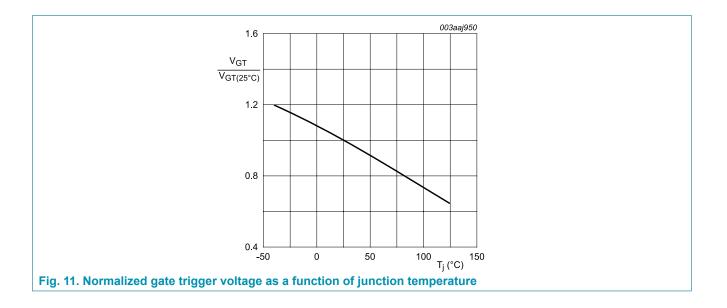
## **11. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	8	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	10	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	22	70	mA
Ι. Ι	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	7	40	μA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	20	60	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	8	40	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	10	60	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	6	30	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>J</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		· ·			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	100	250	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 16 A; $V_{D}$ = 800 V; $I_{G}$ = 0.1 A; $d_{IG}/dt$ = 5 A/µs	-	2	-	μs

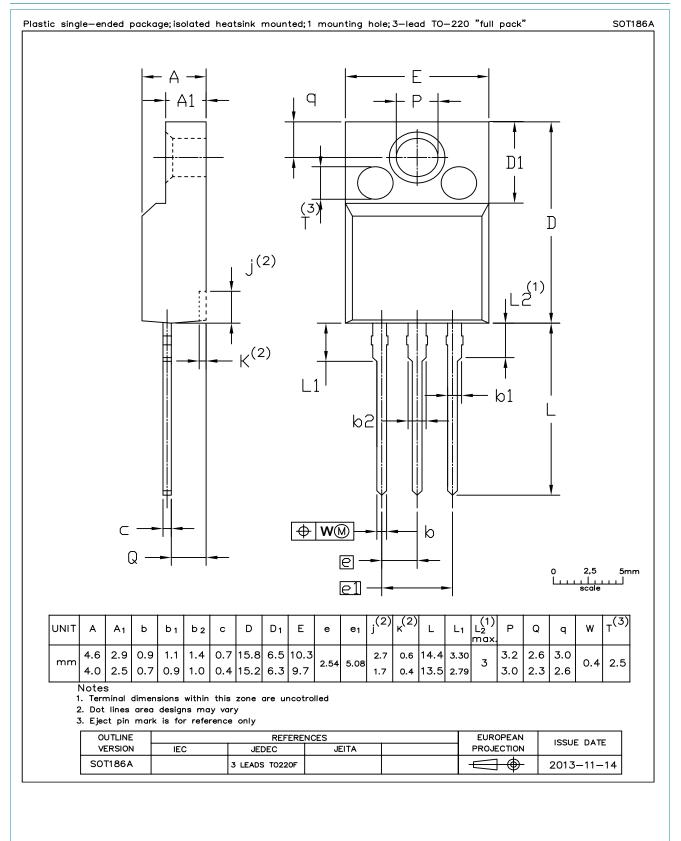


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### 12. Package outline



# 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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